EPSON

S1F75510 Charge-pump DC/DC Converter & Voltage Regulator

Preliminary

DESCRIPTION

The S1F75510 is a power IC designed for use with medium or small capacity TFT–LCD panel modules. A single chip of this IC is capable of generating three different levels of positive and negative output voltages simultaneously, which are necessary to drive the LCD, by use of a single input power of +2.7 through +3.6V. Since the S1F75510 does not require external transistors nor diodes as its voltage conversion circuit, its built-in CMOS transistors constituting a complete charge pump type DC/DC converter, it is most suitable for the purpose of reducing the current consumption levels of the LCD modules.

Moreover, the charge pump type DC/DC converter of the S1F75510 can be operated upon the frequencies, which are to be switched over by the mode changing signals, using either of the built-in clock signals or external clock signals optimal to respective cases.

This function can drastically suppress the current consumption of this IC while under light load state, thus exhibiting very high power conversion efficiencies.

■ FEATURES

- Supply voltage 2.7V to 3.6V single power input
- Self consumption current (normal mode/blank mode) ---- 300µA / 30µA (TBD) Normal mode: Boosting by use of the internal clock

Blank mode: Selectable between boosting by use of the internal clock or by use of the external clock.

- Built-in voltage conversion circuits constituted by charge pump type DC/DC converter,
 - x2 boosting circuit in the positive direction
 - x3 boosting circuit in the positive direction
 - x3 boosting circuit in the negative direction
- Built-in voltage stabilizing circuit
- Capable of outputting the positive supply voltage VOUT2 for the source driver
 - x2 boosting circuit in the positive direction + voltage stabilizing circuit Output voltage: +5.0V ±3% (TBD)
- Capable of outputting the positive supply voltage VOUT3 for the gate driver
 - x3 boosting circuit in the positive direction

Output voltage: +15V

- Vout3 = Vout 2×3
- Capable of outputting the negative supply voltage VOUT4 for the gate driver
 - X3 boosting circuit in the negative direction Output voltage: -10V VOUT4 = VOUT2 X -2
- Built-in electric charge discharging circuit
- Built-in shut down function
- Shipping state ------ SSOP3-24pin
- This IC is not of the radiation resistant design nor of the light resistance design.

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BLOCK DIAGRAM



Fig. 1 Block diagram

■ DESCRIPTIONS FOR THE BLOCK DIAGRAM

(1) CR oscillation circuit

The oscillation circuit is constituted by connecting a resistor between the OSC1 pin and the OSC2 pin. The clock signals being generated by this oscillation circuit will become effective as boosting clock signals while the mode changeover signal MODE is on the VDD level (normal mode) or while the mode changeover signal MODE is on the VDD level (normal mode) or while the mode changeover signal MODE is on the VDD level (normal mode) or while the mode changeover signal MODE is on the VDD level (blank mode · internal clock). When the internal/external clock selection signal OSCSEL is on the VDD level (blank mode · internal clock). When the MODE is set to the VSS level and, at the same time, when the OSCSEL is set to the VSS level (blank mode · external clock), the oscillation will be interrupted.

(2) Mode changeover circuit

The operation modes of the boosting circuit and voltage stabilizing circuit are being switched over by the mode changeover signal MODE. Also, it selects the clock signals to feed to the timing signal forming circuit from either of the external clock signals or internal clock signals.

(3) Timing signal forming circuit

This circuit generates the charge pump boosting clock signals. This circuit outputs timing signals of the clock type (internal clock or external clock) having been selected by the mode changeover circuit to drive respective boosting circuits. When the shut down signal POFFX is set to the Vss level, the timing signal stops to interrupt the boosting operation.

(4) ×2 boosting circuit in the positive direction

This circuit makes x2 boosting in the positive direction by charge pump boosting upon the inputted supply voltage VDD – Vss using the Vss potential as the reference voltage. The x2 boosted output will enter into the voltage stabilizing circuit.

(5) Voltage stabilizing circuit

This circuit generates the positive supply voltage VOUT2 for the source driver. ON the basis of the built-in reference, this circuit stabilizes the output from the above "(4) X2 boosting circuit in the positive direction" by use of the series regulator.

(6) ×3 boosting circuit in the positive direction

This circuit generates the positive supply voltage VOUT3 for the gate driver. This circuit effects X3 boosting in the positive direction by charge pump boosting upon the voltage VOUT2 – VSS using the VSS potential as the reference voltage.

(7) X3 boosting circuit in the negative direction

This circuit generates the negative supply voltage VOUT4 for the gate driver. This circuit effects X3 boosting in the negative direction by charge pump boosting upon the voltage VOUT2 – VSS using the VOUT2 potential as the reference voltage.

(8) Electric charge discharging circuit

This circuit discharges the electric charge remaining in the VOUT3 pin and VOUT4 pin to the VSS level. This circuit will work when the POFFX pin is set to the VSS level.

■ PIN ASSIGNMENT

SSOP3-24pin S1F75510M0A0



Pin No.	Pin name	Pin No.	Pin name	
1	C3N	13	MODE	
2	C3P	14	CL	
3	C4P	15	POFFX	
4	C4N	16	OSC1	
5	Vout3	17	OSC2	
6	Vdd	18	OSCSEL	
7	C1N	19	Vout2	
8	C1P	20	Vout4	
9	Vout1	21	C6P	
10	C2P	22	C6N	
11	C2N	23	C5N	
12	Vss	24	C5P	

■ PIN DESCRIPTION

(1) CR oscillation circuit · Mode changeover circuit · Timing signal forming circuit · Electric charge discharging circuit

Pin name	I/O	Pin No.	Function						
POFFX	I	15	This is the sh	This is the shut down pin. Set it to the VDD level while the IC is in					
			operation. When this signal is set to the VSS level, operations of all						
			the circuits w	the circuits will be interrupted bringing the IC into the shut down					
			state. The ele	ectric charge	discharging circuit discharges the electric				
			charge remai	ning in the Vo	OUT3 pin and VOUT4 pin to the VSS level.				
OSC1	I	16	This is the CI	R oscillation	circuit gate input pin. This is the pin to				
			connect the c	scillation res	istor. Fix it to the VSS level in case the				
			built-in oscilla	ation circuit w	ill not be used.				
OSC2	0	17	This is the CI	R oscillation	circuit drain input pin. Connect the osci-				
			llation resisto	r between th	is pin and the OSC1 pin.				
CL	I	14	This is the bo	osting extern	al clock signal input pin. Input the charge				
			pump clock s	ignals under	the blank mode into this pin.				
MODE	I	13	This is the m	ode changeo	ver pin.				
OSCSEL	I	18	This is the pi	n for selection	n between the internal clock and exter-				
			nal clock sigr	nals.					
			MODE	OSCSEL	Function				
			HIGH(VDD)	HIGH(VDD)	Normal mode				
				LOW(Vss)	The boosting clock signals are being				
				 	generated through the internal				
				 	oscillation.				
				 	The built-in oscillation circuit will ope-				
				1	rate and the voltage stabilizing circuit				
				 	will operate.				
			LOW(Vss)	HIGH(VDD)	Blank mode (internal oscillation)				
				1	The boosting clock signals are being				
				 	generated through the internal				
					oscillation.				
				 	The built-in oscillation circuit will				
				 	operate and the voltage stabilizing				
				 	circuit will operate under low current				
				1	consumption state.				
				LOW(Vss)	Blank mode (external oscillation)				
				1	The boosting clock signals are being				
				 	generated by the external clock.				
				- 	The built-in oscillation circuit will be				
				1	interrupted and the voltage stabiliz-				
				 	ing circuit will operate under low				
				1	current consumption state.				

Pin name	I/O	Pin No.	Function
VOUT1	0	9	This is the output pin of the x2 boosting circuit in the positive
			direction.
C1P	(O)	8	This is the pin to connect the positive side of the VOUT1 output
			voltage generating flying capacitor C1.
C1N	(O)	7	This is the pin to connect the negative side of the VOUT1 output
			voltage generating flying capacitor C1.
C2P	(O)	10	This is the pin to connect the positive side of the VOUT1 output
			voltage generating flying capacitor C2.
C2N	(O)	11	This is the pin to connect the negative side of the VOUT1 output
			voltage generating flying capacitor C2.

(2) X2 boosting circuit in the positive direction

(3) Voltage stabilizing circuit

Pin name	I/O	Pin No.	Function			
VOUT1	I	9	This is the input power pin (+) for the voltage stabilizing circuit.			
			This pin is being connected to the output pin of the x2 boosting			
			circuit in the positive direction internally, inside this IC.			
Vout2	0	19	This is the output pin of the voltage stabilizing circuit.			

(4) X3 boosting circuit in the positive direction

Pin name	I/O	Pin No.	Function
νουτ3	0	5	This is the output pin of the $\times 3$ boosting circuit in the positive
			direction.
C3P	(O)	2	This is the pin to connect the positive side of the VOUT3 output
			voltage generating flying capacitor C3.
C3N	(O)	1	This is the pin to connect the negative side of the VOUT3 output
			voltage generating flying capacitor C3.
C4P	(O)	3	This is the pin to connect the positive side of the VOUT3 output
			voltage generating flying capacitor C4.
C4N	(O)	4	This is the pin to connect the negative side of the VOUT3 output
			voltage generating flying capacitor C4.

Pin name	I/O	Pin No.	Function
Vout4	0	20	This is the output pin of the x3 boosting circuit in the negative
			direction.
C5P	(O)	24	This is the pin to connect the positive side of the VOUT4 output
			voltage generating flying capacitor C5.
C5N	(O)	23	This is the pin to connect the negative side of the VOUT4 output
			voltage generating flying capacitor C5.
C6P	(O)	21	This is the pin to connect the positive side of the VOUT4 output
			voltage generating flying capacitor C6.
C6N	(O)	22	This is the pin to connect the negative side of the VOUT4 output
			voltage generating flying capacitor C6.

(5) X3 boosting circuit in the negative direction

(6) Power pins

Pin name	I/O	Pin No.	Function
Vdd	I	6	This is the input power pin (+).
Vss	I	12	This is the input power pin (–).

■ FUNCTIONAL DESCRIPTION

Operational description

Generating voltage levels are:

- · Positive boosting supply voltage necessary for the voltage stabilizing circuit (VOUT1)
- · Positive stabilized supply voltage necessary for the source driver (Vout2)
- · Positive and negative boosting supply voltages necessary for the gate driver (VOUT3 and VOUT4)

The VOUT1 supply voltage is being generated by the charge pump type DC/DC converter (x2 boosting circuit in the positive direction). It makes x2 boosting in the positive direction of the potential difference occurring between the VDD – Vss using the Vss potential as the reference voltage.

The VOUT2 supply voltages is being generated by the series regulator stabilizing the potential difference occurring between the VOUT1 – VSS using the VSS potential as the reference voltage.

The VOUT3 supply voltage is being generated by the charge pump type DC/DC converter (X3 boosting circuit in the positive direction). It makes X3 boosting in the positive direction of the potential difference occurring between the VOUT2 – Vss using the Vss potential as the reference voltage.

The VouT4 supply voltage is being generated by the charge pump type DC/DC converter (X3 boosting circuit in the negative direction). It makes X3 boosting in the negative direction of the potential difference occurring between the VouT2 – VSS using the VouT2 potential as the reference voltage.

Indicated below is the system configuration diagram for the power circuit.



Fig. 2 System configuration diagram

×3 boosting in the positive direction Vout3 ×2 boosting in the positive direction VOUT1 VOUT2 Voltage stabilizing Vdd Source driver Gate driver Vss **VOUT4** ×3 boosting in the negative direction Power Supply IC (S1F75510)

Indicated below is the potential correlation diagram inside the system as is shown in Fig. 2.

Fig. 3 Potential correlation diagram inside the system

CR oscillation circuit

The S1F75510 incorporates a CR oscillation circuit as the oscillation circuit for the boosting clock signals. This circuit is to be used connecting the external oscillation resistor ROSC between the OSC1 pin and the OSC2 pin. The CR oscillation circuit will stop operation under the blank mode and when using the external clock (MODE = Vss level and OSCSEL = Vss level) or under the shut down state (POFFX = Vss level). Also, the oscillation will be interrupted by setting the OSC1 pin to the VSS level and, at the same time, setting the OSC2 pin into open state.

As the external oscillation resistance, we recommend use of ROSC = 1 M Ω .

Mode changeover circuit

By external settings of the mode changeover signal MODE and the internal/external clock selection signal OSCSEL, the charge pump boosting can be driven under optimum frequencies. Since the current consumption of the IC can be suppressed drastically under the blank mode, it is possible to achieve high power conversion efficiency even under light load operations.

MODE pin	OSCSEL pin	Mode name	Max. output current		Built-in CR oscillation circuit	Built in voltage stabilizing circuit	
	HIGH(VDD)		Vout2:(10mA)	(TBD)			
HIGH(VDD)	HIGH(VDD)	Normal mode	Voυτ3:(100μA)	(TBD)	In operation	In normal operation	
	1		Vout4:(100μA)	(TBD)			
	 	GH(VDD) Blank mode	Vout2:(200μA)	(TBD)	In operation	In low current	
	HIGH(VDD)		Voυτ3:(10μA)	(TBD)			
	I		Vout4:(10μA)	(TBD)		consumption operation	
LOW(Vss)		OW(Vss) Blank mode	Vout2:(200μA)	(TBD)		In low current	
	LOW(Vss)		Voυτ3:(10μA)	(TBD)	In standstill		
			Vout4:(10μA)	(TBD)		consumption operation	

• Timing signal forming circuit

This circuit generates the clock signals necessary for charge pump boosting using the internal oscillation or using external clock signals.

Two different types of capacitors are being used as the charge pump capacitors, one being the flying capacitor which shifts between the charging state and the discharging state and the other being the smoothing capacitor which preserves the electric charge. The operating frequency of the flying capacitor should equal to the frequency of the charge pump clock being generated by this timing signal forming circuit.

Under the shut down state (POFFX = Vss level), the charge pump clock stops operation and all the boosting operations of this IC will be interrupted. The operating frequencies of the flying capacitor are as follows.

MODE pin	OSCSEL	Mode name	Operating frequencies of the flying capacitor				
	pin	mode name	×2 boosting in	×3 boosting in	×3 boosting in		
	1		the positive direction	the positive direction	the negative direction		
	HIGH(VDD)	Normal mode	(TBD) kHz	(TBD) kHz	(TBD) kHz		
HIGH(VDD)	LOW(Vss)	Normal mode	(Typ.10 kHz)	(Typ.10 kHz)	(Typ.10 kHz)		
		IIGH(VDD) Blank mode	(TBD) kHz	(TBD) kHz	(TBD) kHz		
	(יטטי)		(Typ.625 Hz)	(Typ.625 Hz)	(Typ.625 Hz)		
LOW(Vss)	LOW(Vss)	Blank mode CL=(TBD) Hz (Min.300 Hz)	(TBD) Hz (Min.150 Hz)	(TBD) Hz (Min.150 Hz)	(TBD) Hz (Min.150 Hz)		

● ×2 boosting circuit in the positive direction

The x2 boosting circuit in the positive direction generates the voltages necessary to input into the voltage stabilizing circuit. It makes x2 boosting in the positive direction of the potential difference occurring between the VDD - VSS using the VSS potential as the reference voltage to output through the VOUT1 pin.

Under the blank mode, since the boosting operation is being carried out with the flying capacitor C2 stopping its operation, the current consumption can be suppressed accordingly.

The theoretical equation (output voltage value under the idealistic non-load state) for the VOUT1 becomes as follows:

 $VOUT1 = (VDD - VSS) \times 2$

Actually, when a load is connected to the VOUT1, the output voltage will drop to the value represented by the equation indicated below.

VOUT1 = (VDD - VSS) X 2 - RVOUT1 X IVOUT1

RVOUT1 : Output impedance of the x2 boosting circuit in the positive direction

IVOUT1 : Load current

Voltage stabilizing circuit

The voltage stabilizing circuit stabilizes the voltage being output through the VOUT1 pin by the series regulator to output the positive supply voltage for the source driver through the VOUT2 pin.

The output voltage setting for the VOUT2 pin should be Typ. +5.0V (TBD).

Since it is necessary to let the VOUT1 satisfy the correlation of "VOUT1 > VOUT2 + 0.1V" in order to obtain normal output voltage value through the VOUT2 pin, use the IC within the range of the max. load current (7.3).

The circuit configuration - connection diagram for the voltage stabilizing circuit is as follows:



Fig. 4 Configuration diagram of the voltage stabilizing circuit

• ×3 boosting circuit in the positive direction

The X3 boosting circuit in the positive direction generates the VOUT3 output voltage, means the positive supply voltage for the gate driver. It makes X3 boosting in the positive direction of the potential difference occurring between the VOUT2 – VSS using the VSS potential as the reference voltage, by charge pump boosting, to output through the VOUT3 pin.

The theoretical equation (output voltage value under the idealistic non-load state) for the VOUT3 becomes as follows:

 $VOUT3 = (VOUT2 - VSS) \times 3$

Actually, when a load is connected to the VOUT3, the output voltage will drop to the value represented by the equation indicated below.

VOUT3 = (VOUT2 - VSS) × 3 - (RVOUT3 × IVOUT3)

RVOUT3 : Output impedance of the X3 boosting circuit in the positive direction IVOUT3 : Load current

It means that the VOUT3 voltage will drop by the load.

To acquire desired output voltage, use the IC within the range of the specified load (7.3).

● ×3 boosting circuit in the negative direction

The X3 boosting circuit in the negative direction generates the VOUT3 output voltage, means the negative supply voltage for the gate driver. It makes X3 boosting in the negative direction of the potential difference occurring between the VOUT2 – VSS using the VOUT2 potential as the reference voltage, by charge pump boosting, to output through the VOUT4 pin.

The theoretical equation (output voltage value under the idealistic non-load state) for the VOUT4 becomes as follows:

VOUT4 = (VOUT2 - VSS) \times (-2) (The voltage value using the VSS potential as the reference voltage)

Actually, when a load is connected to the VOUT4, the output voltage will drop to the value represented by the equation indicated below.

 $VOUT4 = (VOUT2 - VSS) \times (-2) - (RVOUT4 \times IVOUT4)$

RVOUT4 : Output impedance of the X3 boosting circuit in the negative direction IVOUT4 : Load current

It means that the VOUT4 voltage will drop by the load.

To acquire desired output voltage, use the IC within the range of the specified load (7.3).

Electric charge discharging circuit

The electric charge discharging circuit discharges the electric charge remaining in the VOUT3 pin and VOUT4 pin to the Vss level.

This circuit starts operation when the POFFX pin is set to the Vss level.

The discharging sequence and the discharging impedance are according to the (TBD).



■ ABSOLUTE MAXIMUM RATINGS

ltem	Symbol	Rat	ing	L los it	Applicable	Demenie
item	Symbol	Min.	Max.	Unit	pin	Remarks
Input supply voltage	Vdd	- 0.3	4.0	V	Vdd	_
Output voltage 1	VOUT1	- 0.3	7.5	V	VOUT1	—
Output voltage 2	Vout2	- 0.3	7.5	V	VOUT2	_
Output voltage 3	Vout3	- 0.3	22.5	V	Vout3	_
Output voltage 4	Vout4	- 15.0	0.3	V	VOUT4	_
Input pin voltage 1	Vin	- 0.3	VDD + 0.3	V	<note 1=""></note>	_
Input current	IVdd		(TBD)	mA	Vdd	
Output current 1	IVOUT1		(TBD)	mA	VOUT1	_
Output current 2	IVOUT2		(TBD)	mA	VOUT2	_
Output current 3	Ινουτ3		(TBD)	mA	Vout3	_
Output current 4	IVOUT4		(TBD)	mA	VOUT4	_
Allowable dissipation	PD	_	(TBD)	mW	_	Ta ≤ 55°C
Operating temperature	Topr	- 30	85	°C	—	_
Storage temperature	Tstg	- 55	150	°C	—	_
Soldering temperature	Tsol	_	260.10	°C·s	—	At leads
and time						

<Note 1> The applicable pins are POFFX, OSC1, CL, MODE and OSCSEL.

<Note 2> Do not apply external voltage to the output pins and the pin connecting to the capacitor.

<Note 3> Use of the IC under any conditions exceeding the above absolute maximum ratings may cause malfunctioning or permanent breakdown. Or, even if the IC may operate normally temporarily, the reliability may greatly drop.

ELECTRICAL CHARACTERISTICSDC characteristics

In case particular designations are not made (Note 1): Ta = -10 to $+70^{\circ}C$

Item	O week al	O an dition a		Rating			Describe
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Remarks
Input supply voltage	Vdd	Applicable pin: VDD	(TBD)	3.0	3.6	V	_
High level input voltage	Vih	—	0.8Vdd	_	Vdd	V	2
Low level input voltage	VIL	—	0	_	0.2Vdd	V	2
Input leak current 1	ILKI1	$VSS \le VI \le VDD,$	- 0.5	_	0.5	μΑ	2
		VDD = (TBD) to 3.6V					
Current consumption 1	IOPR1	VDD = 3.0V, no load		(TBD)	(TBD)	μΑ	
		Under the normal mode		(300)			
Current consumption 2	IOPR2	VDD = 3.0V, no load		(TBD)	(TBD)	μΑ	
		Under the blank mode		(30)			
		CL = (TBD) kHz					
Power conversion efficiency 1	Peff1	VDD = 3.0V	(TBD)	(TBD)	(TBD)	%	3
(Overall efficiency including		Under the normal mode					
the stabilized outputs)							
Power conversion efficiency 2	Peff2	VDD = 3.0V	(TBD)	(TBD)	(TBD)	%	4
(Overall efficiency including		Under the blank mode					
the stabilized outputs)		CL = (TBD) kHz					
Resting current	IQ	VDD = 3.6V	_		(TBD)	μΑ	—
		POFFX = LOW			(1.0)		

<Note 1> Conditions on the operation mode, external parts constant, pins, etc. in case particular designations are not made are as follows.

Connection and parts constant: Standard connection 1, 10.1MODE pin: MODE = HIGH (Normal mode)CL pin: CL = LOW (Fixed voltage)

<Note 2> The applicable pins are XDIS, SSLP, PCK1 and CNT

<Note 3> Load conditions: IVOUT2 = (TBD)mA, IVOUT3 = (TBD) μ A, IVOUT4 = (TBD) μ A

Conversion efficiency = [(VOUT2 X IVOUT2) + (VOUT3 X IVOUT3) + (VOUT4 X IVOUT4)] / (VDD* X IVDD*) X 100 <Note 4> Load conditions: IVOUT2 = (TBD)μA, IVOUT3 = (TBD)μA, IVOUT4 = (TBD)μA

Conversion efficiency = [(VOUT2 X IVOUT2) + (VOUT3 X IVOUT3) + (VOUT4 X IVOUT4)] / (VDD* X IVDD*) X 100

• Characteristics of ×2 boosting in the positive direction + stabilized output

Ta = -10 to +70°C

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Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Remarks
VOUT1 output impedance	RVOUT1-1	Applicable pin:	—	(TBD)	(TBD)	Ω	5
(Normal mode)		VOUT1					
VOUT1 output impedance	RVOUT1-2	Applicable pin:	—	(TBD)	(TBD)	Ω	6
(Blank mode)		VOUT1					
Vout2	Vout2	Applicable pin:	(TBD)	(TBD)	(TBD)	V	7
Stabilized output voltage		Vout2	(4.90)	(5.00)	(5.20)		
VOUT2 Stabilized output	RV0UT2	Applicable pin:	_		10	Ω	8
saturated resistance		Vout2					

<Note 5> VDD = (TBD)V to 3.6V, Load condition: IVOUT1 = (TBD)mA

<Note 6> VDD = (TBD)V to 3.6V, Load condition: IVOUT1 = (TBD)mA

<Note 7> VDD = (TBD)V to 3.6V, Load condition: IVOUT2 = (TBD)mA

<Note 8> VDD = (TBD)V to 3.6V, Load condition: IVOUT2 = (TBD)mA

• Characteristics of ×3 boosting in the positive direction and ×3 boosting in he negativet direction

 $Ta = -10 \text{ to } +70^{\circ}C$

ltem	Symbol	Conditions	Rating			Unit	Remarks
			Min.	Тур.	Max.	Unit	Remarks
VOUT3 output impedance	RVOUT3-1	Applicable pin:	_	(TBD)	(TBD)	Ω	9
(Normal mode)		Vout3					
VOUT3 output impedance	RVOUT3-2	Applicable pin:	_	(TBD)	(TBD)	Ω	10
(Blank mode)		Vout3					
VOUT4 output impedance	RVOUT4-1	Applicable pin:		(TBD)	(TBD)	Ω	11
(Normal mode)		Vout4					
Vouta output impedance	RVOUT4-2	Applicable pin:	_	(TBD)	(TBD)	Ω	12
(Blank mode)		Vout4					

<Note 9> VDD = (TBD)V to 3.6V, Load condition: IVOUT3 = (TBD) μ A <Note 10> VDD = (TBD)V to 3.6V, Load condition: IVOUT3 = (TBD) μ A <Note 11> VDD = (TBD)V to 3.6V, Load condition: IVOUT4 = (TBD) μ A <Note 12> VDD = (TBD)V to 3.6V, Load condition: IVOUT4 = (TBD) μ A

• AC characteristics

Measurement conditions for the AC characteristics

• Input signal level VIH = 0.8 VDD (V)

VIL = 0.2 VDD (V)

- \cdot Input signal rise time Tr = Max. 100ns
- · Input signal fall time Tf = Max. 100ns

VDD = (TBD) to 3.6V, VSS = 0VTa = -10 to +70°C

CL inputting timing



Item	Symbol	Rating			L lusit	Applicable	Domoriko	
		Min.	Тур.	Max.	Unit	pin	Remarks	
CL cycle	tcck	(TBD)	(TBD)	(TBD)	μs			
CL High pulse duration	twнск	(TBD)			ns	CL	—	
CL Low pulse duration	twick	(TBD)	_	_	ns			

■ REFERENCE EXTERNAL CONNECTION (AN EXAMPLE)

Standard connection 1



DIMENSIONAL OUTLINE DRAWING



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